



JMT90



Electrical Characteristics (@ T_C = 25°C unless otherwise specified)

Parameter	Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	
Peak forward voltage	I _T =270A, t _P =380μs	V _T			1.80	V
Repetitive peak off-state current	V _D = V _{DRM} , T _{vj} = 25	I _{DRM}			100	μA
	V _D = V _{DRM} , T _{vj} = 125				40	mA
Reverse leakage current	V _R = V _{RRM} , T _{vj} = 25	I _{RRM}			100	μA
	V _R = V _{RRM} , T _{vj} = 125				40	mA
Threshold voltage	For power loss calculation only T _{vj} = 125 ,	V _{TO}			0.9	V
Dynamic resistance	T _{vj} = 125 ,	r _T			3.1	m
Triggering gate current	V _D =12V R _L =30	I _{GT}	20		120	mA
Holding current	I _T =1A	I _H			250	mA
Latching current	I _G =1.2 I _{GT}	I _L			300	mA
Critical rate of rise of voltage	V _D =2/3V _{DRM} T _{vj} =125 Gate Open	dv/dt	1000			V/μs
Triggering gate voltage	V _D =12V R _L =30	V _{GT}			1.8	V
Non triggering gate voltage	V _D =0.5V _{DRM} T _{vj} =125	V _{GD}	0.25			V

Thermal Characteristics (@ T_C = 25°C unless otherwise specified)

Parameter	Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction to case	per Thyristor	R _{th(j-c)}		0.285		/W
Thermal resistance, case to heatsink	per Thyristor	R _{th(c-s)}		0.14		/W

2 (i) 2.1 Tc 13 >>BDC 0.004 Tc -0.046.76 0.4 re f 3 0 Td 2-0 0 9 62o4 (c)-1Cc bL C

Mounting torque



Ordering Information

Device	Marking	Package	Weight	Inner Box	
--------	---------	---------	--------	-----------	--



Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Semiconductor Co., Ltd assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. This infor